

SMD Schottky Barrier Rectifiers

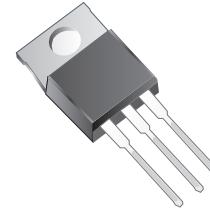
COMCHIP
SMD Diodes Specialist

MBR2030CT-G Thru. MBR20150CT-G

Voltage: 30 to 150 V

Current: 20.0 A

RoHS Device

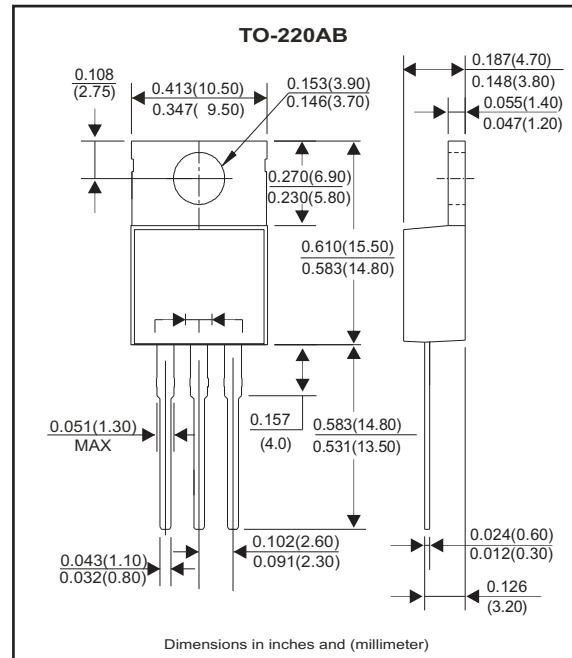


Features

- Metal of silicon rectifier, majority carrier conduction.
- Guard ring for transient protection.
- Low power loss, high efficiency.
- High current capability, low VF.
- High surge capacity.
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.

Mechanical Data

- Case: TO-220AB, molded plastic
- Epoxy: UL 94-V0 rate flame retardant.
- Polarity: As marked on the body.
- Mounting position: Any
- Weight: 2.24 grams



Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load derate current by 20%.

Parameter	Symbol	MBR 2030CT-G	MBR 2040CT-G	MBR 2050CT-G	MBR 2060CT-G	MBR 2080CT-G	MBR 20100CT-G	MBR 20150CT-G	Unit
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	30	40	50	60	80	100	150	V
Maximum RMS Voltage	V_{RMS}	21	28	35	42	56	70	105	V
Maximum DC Blocking Voltage	V_{DC}	30	40	50	60	80	100	150	V
Maximum Average Forward Rectified Current (See Fig.1)	$I_{(AV)}$	20.0							A
Peak Forward Surge Current , 8.3ms Single Half Sine-Wave Super Imposed On Rated Load(JEDEC Method)	I_{FSM}	120							A
Peak Forward Voltage (Note 1)	V_F IF=10A@ $T_J= 25^\circ\text{C}$	-	0.80	0.85	0.95				V
	IF=10A@ $T_J=125^\circ\text{C}$	0.57	0.70	0.75	0.85				
	IF=20A@ $T_J= 25^\circ\text{C}$	0.84	0.95	0.95	1.05				
	IF=20A@ $T_J=125^\circ\text{C}$	0.72	0.85	0.85	0.95				
Maximum DC Reverse Current at Rate DC Blocking Voltage	I_R $@ T_J= 25^\circ\text{C}$	0.10	0.10	0.10	0.10	0.10	0.10	0.10	mA
	$@ T_J= 125^\circ\text{C}$	15.0	10.0	7.50	5.00	5.00	5.00	5.00	
Typical Junction Capacitance (Note2)	C_J	400			320				pF
Typical Thermal Resistance (Note3)	$R_{\theta JC}$		1.50			3.50			$^\circ\text{C/W}$
Operating Temperature Range	T_J			-55 to +150					$^\circ\text{C}$
Storage Temperature Range	T_{STG}			-55 to +175					$^\circ\text{C}$

NOTES:

1. 300us pulse width,2% duty cycle.
2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
3. Thermal resistance junction to case.

REV:A

SMD Schottky Barrier Rectifiers

RATING AND CHARACTERISTIC CURVES (MBR2030CT-G Thru. MBR20150CT-G)

FIG.1- Forward Current Derating Curve

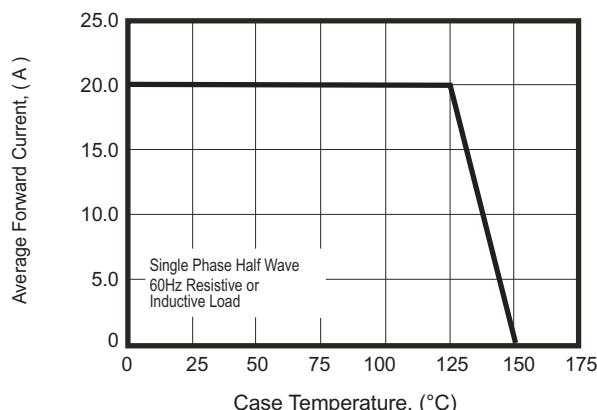


FIG.2- Maximum Non-Repetitive Surge Current

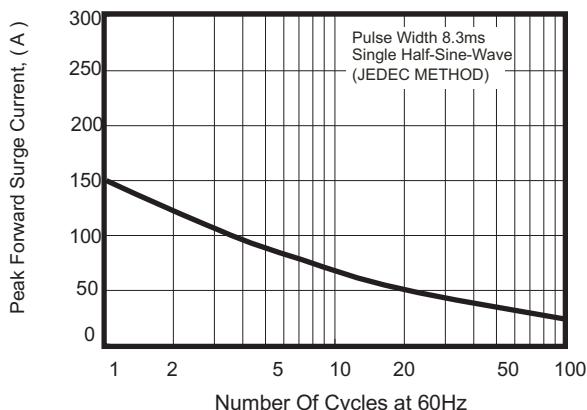


FIG.3- Typical Rever Characteristics

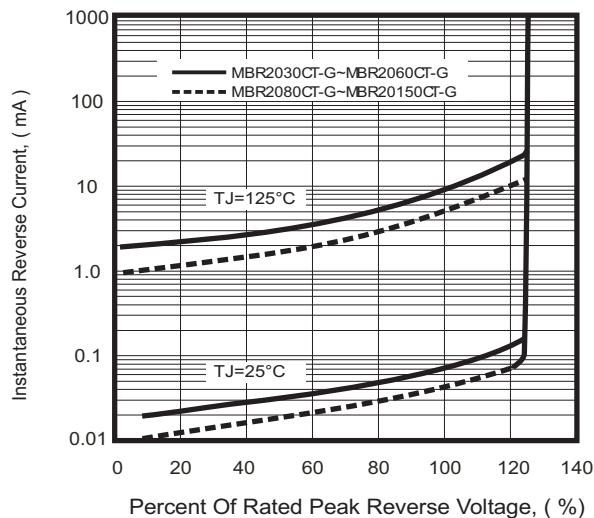


FIG.4- Typical Forward Characteristics

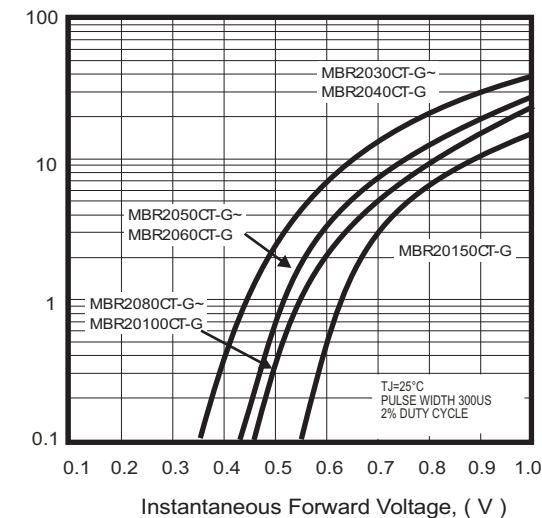
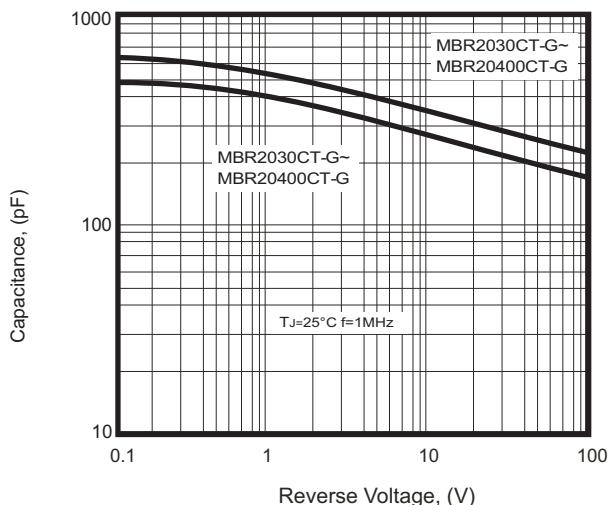
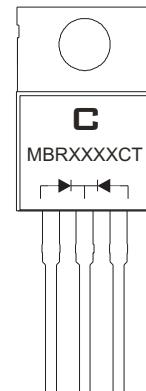


FIG.5- Typical Junction Capacitance



Marking Code

Part Number	Marking code
MBR2030CT-G	MBR2030CT
MBR2040CT-G	MBR2040CT
MBR2050CT-G	MBR2050CT
MBR2060CT-G	MBR2060CT
MBR2080CT-G	MBR2080CT
MBR2100CT-G	MBR2100CT
MBR2150CT-G	MBR2150CT



XXXX = Product type marking code
C = Compchip Logo

Standard Package

Case Type	TUBE PACK		
	TUBE (EA)	Box (EA)	CARTON (EA)
TO-220AB	50	2,000	8,000